

Process		9 μ m Thick Photoresist Process
		AZ 9260
Dehydration Bake (hot plate)	temp ($^{\circ}$ C)	200
	time (min)	5
HMDS vapor prime	time (min)	3
Spin coating AZ9260	Speed/acc (rpm)	300
	time (s)	10
	speed (rpm)	2000
	acceleration (rpm/s)	5000
	time (s)	60
Wait	time (s)	60
Soft-bake (hotplate)	temp ($^{\circ}$ C)	110
	time (s)	165
Expose (12mW/cm ²)	mode	SC Multiple exposures 3 cycles of 14 sec each w/ 10 s gap
	time (s)	42
Develop	developer	AZ 400K
	developer: di water ratio	1:4
	time (min) (approx.)	2 $\frac{3}{4}$
Rinse in DI water	time (min)	2

NB:

1. Use a minimum of 100 ml of AZ 400K developer for a 4-inch wafer to avoid the slow-down of the development rate due to insufficient developer quantity.
2. These results are based on a Silicon substrate. Films present on substrates and/or other types of substrates may affect the exposure and/or development time. Adjust as needed.